## Inseto - Silicon Carbide SiC Selection Nomenclatures

## Wafer Wafer diameter Material **Micropipe density** (mm) Other Crystallographic SiC orientation Resistivity 50 LM laser <1.cm-2 76 Polish mark (0001)V doped >1E7 100 <5.cm-2 **BS LM** (0001)4 deg Off axis un doped 150 SSP backside LM <15.cm-2 0.015-0028 DSP 200 <30.cm-2 500+/->1E7 100 mm SiC SI (0001)ABCB 4H **CVD** PRODUCTION <5.cm-2 DSP SSF LM 25 µm ohm.cm Stacking Thickness **Alignment Fiducial** Туре Growth Grade sequence/polytype method SI - Semi SSF; SEMI std flat Zero MP μm Insulating 2 SSF; SEMI std flats ABCB 4H PRODUCTION mm CVD N type -SSN; SEMI std notch RESEARCH (=1000µm) **Sublimation ABCACB 6H** undoped None DUMMY

Inseto (UK) Limited Unit 25 Focus Way Andover, SP10 5NY United Kingdom +44 (0)1264 334505 - enquiries@inseto.co.uk – www.inseto.co.uk The wafer in the example is a 100mm dia, SiC Wafer, Semi Insulating type, (0001) orientation, ABCB 4H stacking sequence/polytype, CVD grown, Production grade, MPD <5.cm-2, with resistivity of >1E7ohm.cm V doped, thickness is 500+/-25um and it is double side polished with SEMI std flat.

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The wafer also has a Laser mark for identification. Note with SiC this is usually how the S or C faces are identified according to LM location